



SANYO Semiconductors

# DATA SHEET

An ON Semiconductor Company

## ECH8662 — N-Channel Silicon MOSFET — General-Purpose Switching Device Applications

### Features

- Low ON-resistance
- 2.5V drive
- Halogen free compliance
- Protection diode in

### Specifications

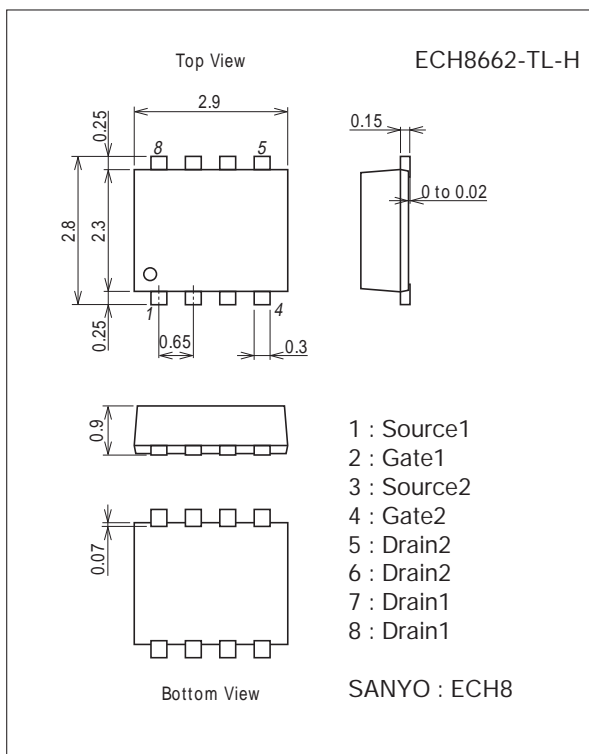
Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V <sub>DSS</sub>		40	V
Gate-to-Source Voltage	V <sub>GSS</sub>		±10	V
Drain Current (DC)	I <sub>D</sub>		6.5	A
Drain Current (Pulse)	I <sub>DP</sub>	PW≤10μs, duty cycles≤1%	40	A
Allowable Power Dissipation	P <sub>D</sub>	When mounted on ceramic substrate (900mm <sup>2</sup> ×0.8mm) 1unit	1.3	W
Total Dissipation	P <sub>T</sub>	When mounted on ceramic substrate (900mm <sup>2</sup> ×0.8mm)	1.5	W
Channel Temperature	T <sub>ch</sub>		150	°C
Storage Temperature	T <sub>stg</sub>		-55 to +150	°C

### Package Dimensions

unit : mm (typ)

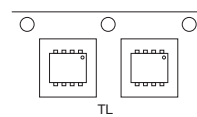
7011A-001



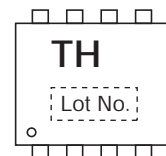
### Product & Package Information

- Package : ECH8
- JEITA, JEDEC : -
- Minimum Packing Quantity : 3,000 pcs./reel

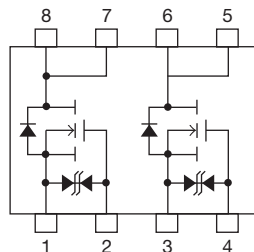
### Packing Type : TL



### Marking



### Electrical Connection

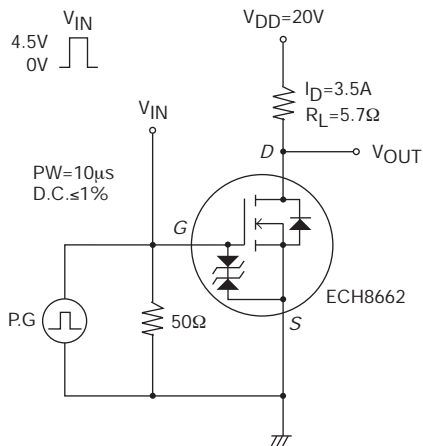


# ECH8662

## Electrical Characteristics at Ta=25°C

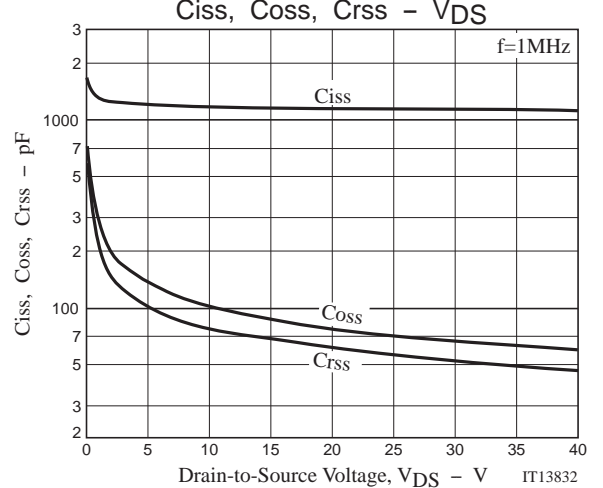
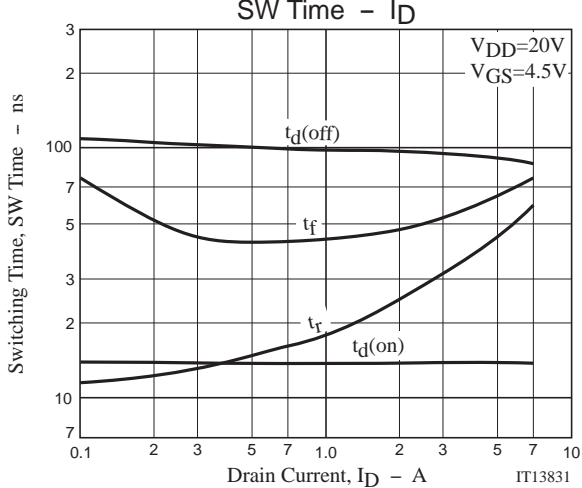
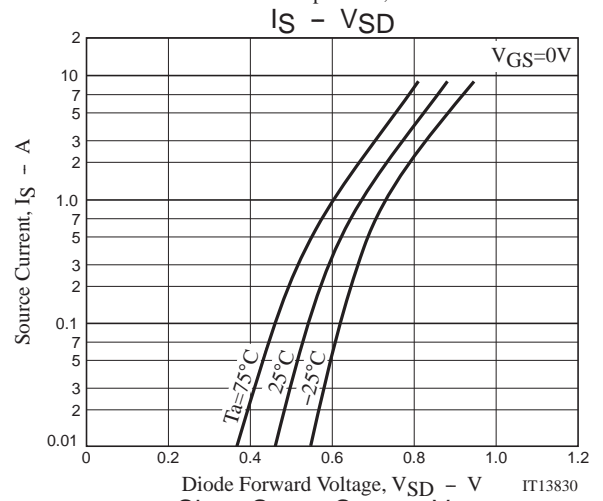
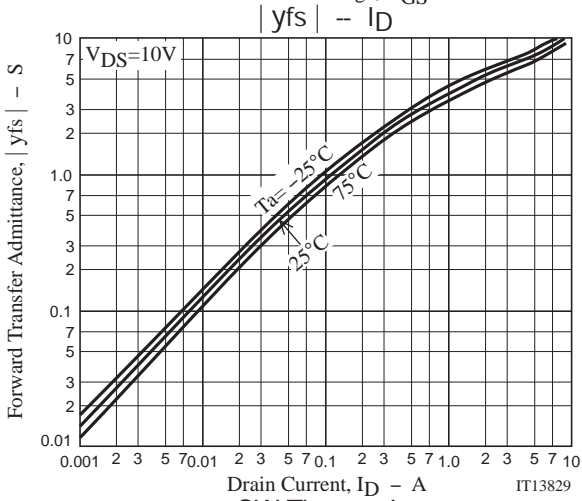
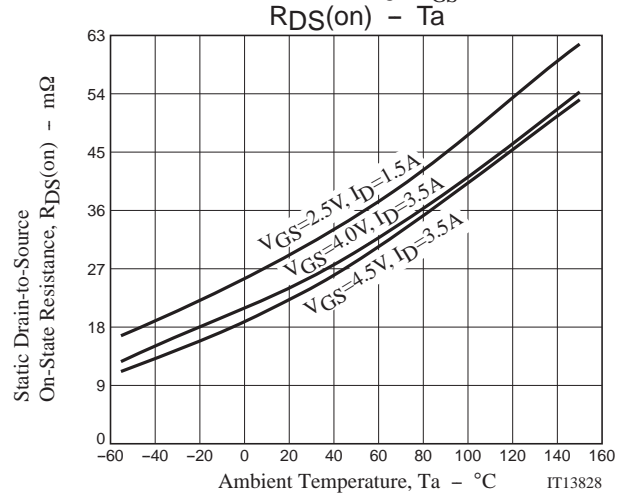
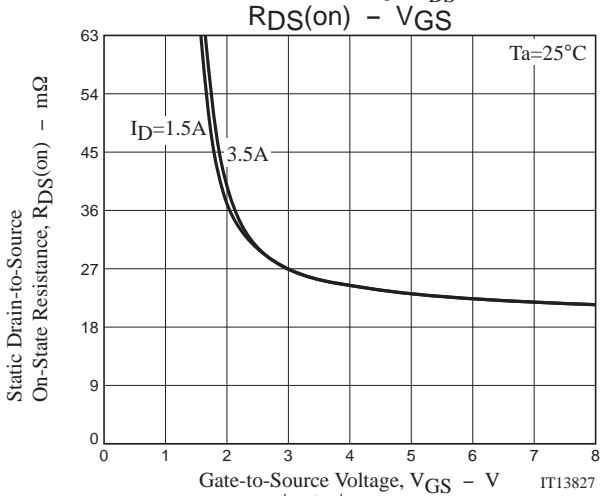
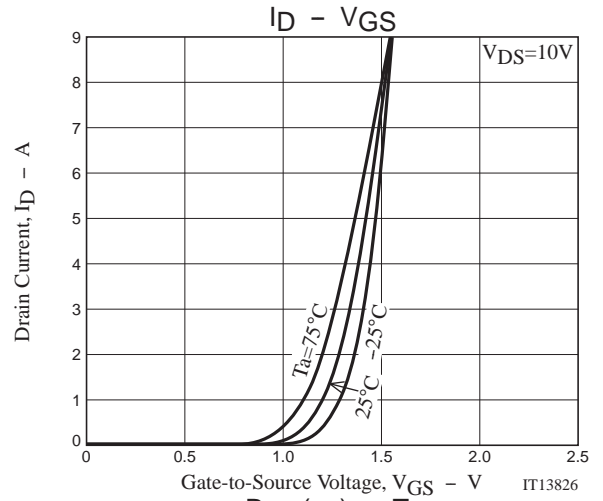
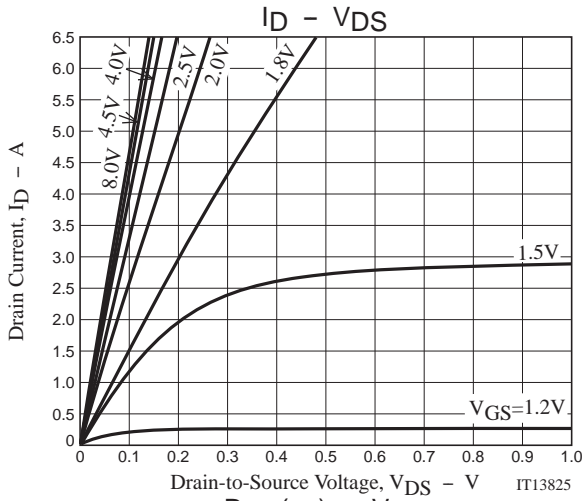
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	V(BR)DSS	I <sub>D</sub> =1mA, V <sub>GS</sub> =0V	40			V
Zero-Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =40V, V <sub>GS</sub> =0V			1	μA
Gate-to-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±8V, V <sub>DS</sub> =0V			±10	μA
Cutoff Voltage	V <sub>GS(off)</sub>	V <sub>DS</sub> =10V, I <sub>D</sub> =1mA	0.4		1.3	V
Forward Transfer Admittance	y <sub>fs</sub>	V <sub>DS</sub> =10V, I <sub>D</sub> =3.5A	3.9	6.5		S
Static Drain-to-Source On-State Resistance	R <sub>DS(on)1</sub>	I <sub>D</sub> =3.5A, V <sub>GS</sub> =4.5V		23	30	mΩ
	R <sub>DS(on)2</sub>	I <sub>D</sub> =3.5A, V <sub>GS</sub> =4V		25	33	mΩ
	R <sub>DS(on)3</sub>	I <sub>D</sub> =1.5A, V <sub>GS</sub> =2.5V		30	42	mΩ
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =20V, f=1MHz		1130		pF
Output Capacitance	C <sub>oss</sub>	V <sub>DS</sub> =20V, f=1MHz		77		pF
Reverse Transfer Capacitance	C <sub>rss</sub>	V <sub>DS</sub> =20V, f=1MHz		60		pF
Turn-ON Delay Time	t <sub>d(on)</sub>	See specified Test Circuit.		14		ns
Rise Time	t <sub>r</sub>			34		ns
Turn-OFF Delay Time	t <sub>d(off)</sub>			93		ns
Fall Time	t <sub>f</sub>			55		ns
Total Gate Charge	Q <sub>g</sub>				12	
Gate-to-Source Charge	Q <sub>gs</sub>	V <sub>DS</sub> =20V, V <sub>GS</sub> =4.5V, I <sub>D</sub> =6.5A		2.2		nC
Gate-to-Drain "Miller" Charge	Q <sub>gd</sub>			3.4		nC
Diode Forward Voltage	V <sub>SD</sub>		I <sub>S</sub> =6.5A, V <sub>GS</sub> =0V		0.85	1.2

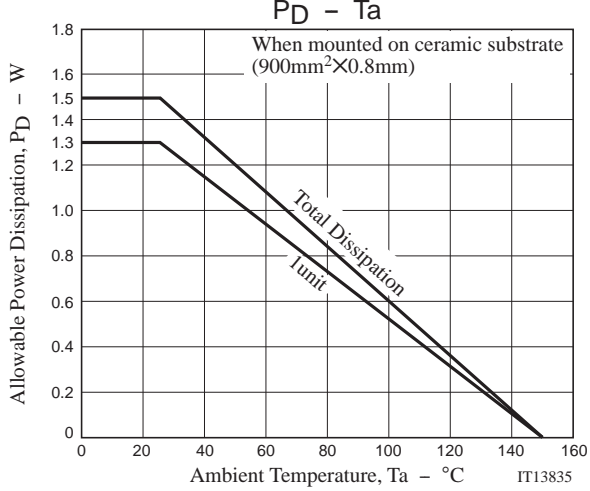
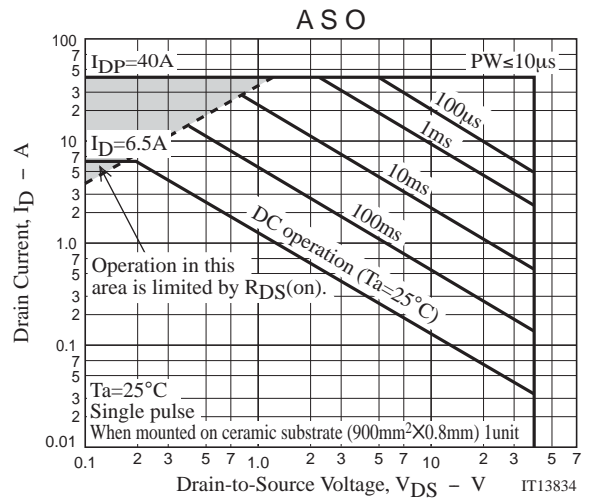
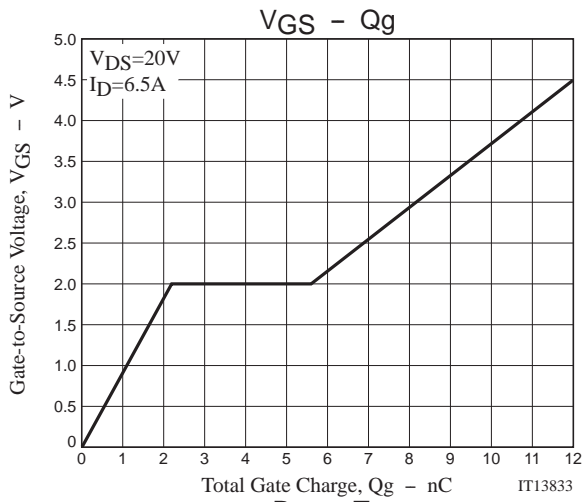
## Switching Time Test Circuit



## Ordering Information

Device	Package	Shipping	memo
ECH8662-TL-H	ECH8	3,000pcs./reel	Pb Free and Halogen Free





Embossed Taping Specification

ECH8662-TL-H

1. Packing Format

Package Name	Carrier Tape Type	Maximum Number of devices contained (pcs)			Packing format	
		Reel	Inner box	Outer box	Inner BOX (C-1)	Outer BOX (A-7)
ECH8	CPH6	3,000	15,000	90,000	5 reels contained Dimensions:mm (external) 183×72×185	6 inner boxes contained Dimensions:mm (external) 440×195×210

Reel label, Inner box label  
(unit :mm)

Outer box label

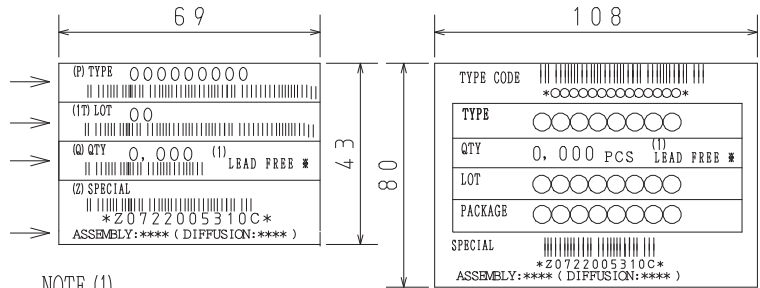
It is a label at the time of factory shipments.  
The form of a label may change in physical distribution process.

Packing method



Reel label

Type No.  
LOT No.  
Quantity  
Origin



NOTE (1)

The LEAD FREE \* description shows that the surface treatment of the terminal is lead free.

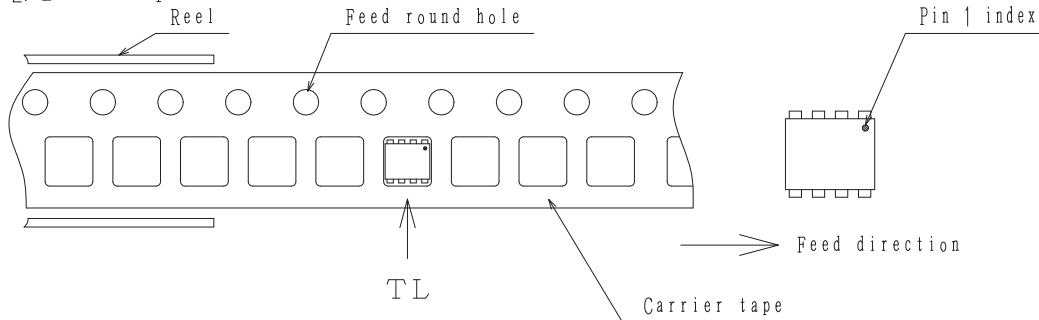
Label	JEITA Phase
LEAD FREE 3	JEITA Phase 3A
LEAD FREE 4	JEITA Phase 3

2. Taping configuration

2-1. Carrier tape size (unit:mm)

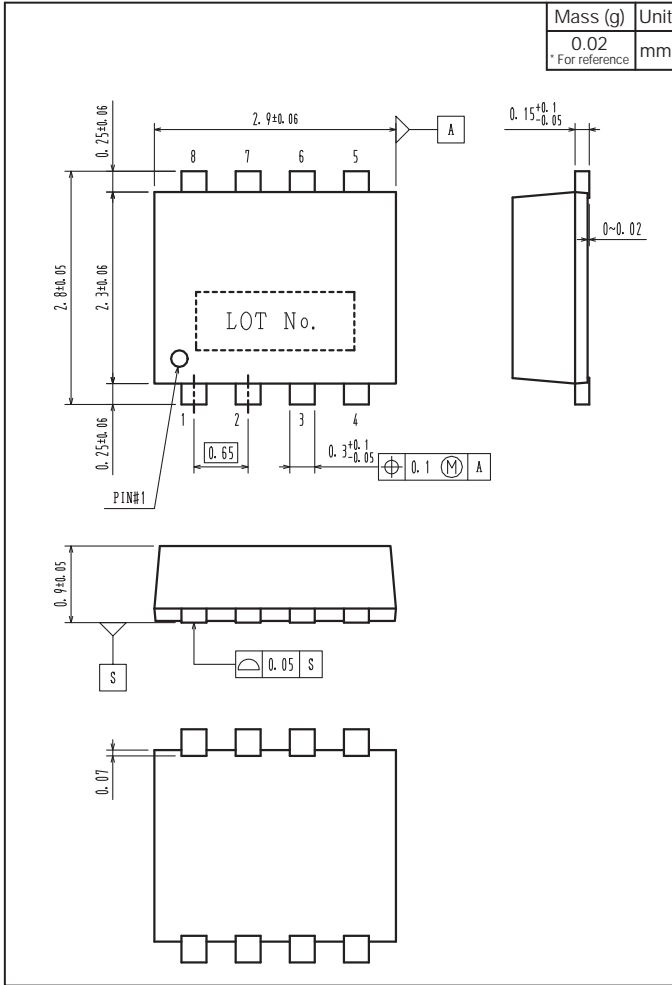


2-2. Device placement direction

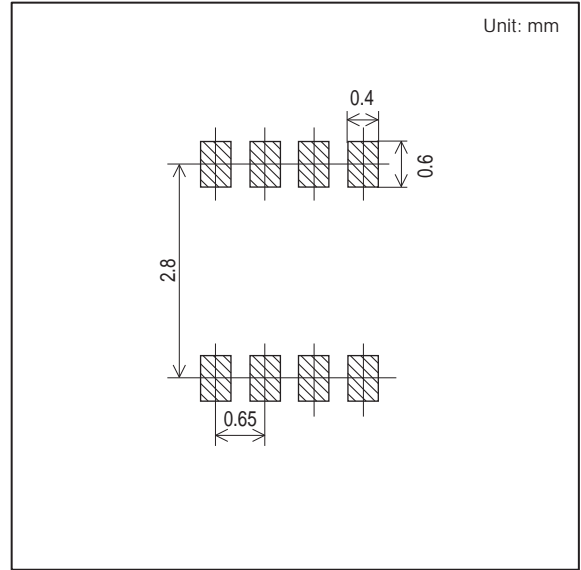


Those with pin 1 index on the feed hole side.....TL

Outline Drawing  
ECH8662-TL-H



Land Pattern Example



Note on usage : Since the ECH8662 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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